Lattice Semiconductor Corporation - LFE5UM-45F-7MG285I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	11000
Number of Logic Elements/Cells	44000
Total RAM Bits	1990656
Number of I/O	118
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	285-LFBGA, CSPBGA
Supplier Device Package	285-CSFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5um-45f-7mg285i

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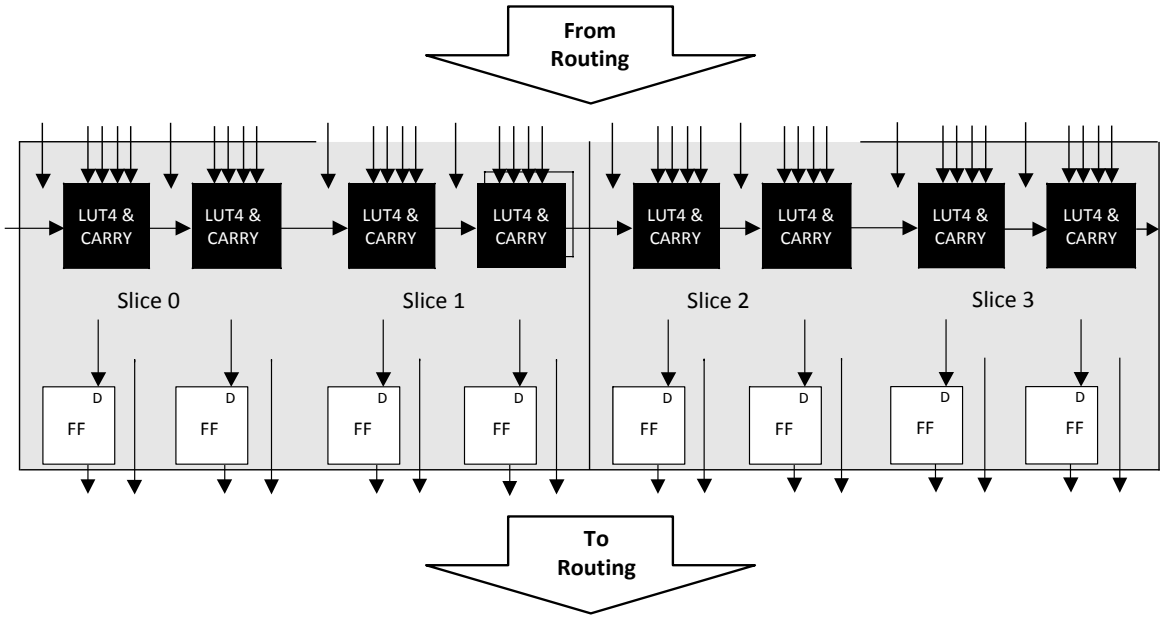

Figure 2.2. PFU Diagram

2.2.1. Slice

Each slice contains two LUT4s feeding two registers. In Distributed SRAM mode, Slice 0 through Slice 2 are configured as distributed memory, and Slice 3 is used as Logic or ROM. Table 2.1 shows the capability of the slices along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2.1. Resources and Modes Available per Slice

Slice	PFU (Used in Distributed SRAM)		PFU (Not used as Distributed SRAM)	
	Resources	Modes	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 1	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 2	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2.3 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks.

Each slice has 14 input signals, 13 signals from routing and one from the carry-chain (from the adjacent slice or PFU). There are five outputs, four to routing and one to carry-chain (to the adjacent PFU). There are two inter slice/ PFU output signals that are used to support wider LUT functions, such as LUT6, LUT7 and LUT8. Table 2.2 and Figure 2.3 list the signals associated with all the slices. Figure 2.4 on page 16 shows the connectivity of the inter-slice/PFU signals that support LUT5, LUT6, LUT7 and LUT8.

Table 2.6. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

2.8.2. Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

2.8.3. RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

2.8.4. Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

2.8.5. Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports the following forms of write behavior for single port or dual port operation:

- **Normal** – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- **Write Through** – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.
- **Read-Before-Write** – When new data is written, the old content of the address appears at the output. This mode is supported for x9, x18, and x36 data widths.

In Figure 2.15, note that A_ALU, B_ALU and C_ALU are internal signals generated by combining bits from AA, AB, BA BB and C inputs. For further information, refer to ECP5 and ECP5-5G sysDSP Usage Guide (TN1267).

The ECP5/ECP5-5G sysDSP block supports the following basic elements.

- MULT (Multiply)
- MAC (Multiply, Accumulate)
- MULTADDSUB (Multiply, Addition/Subtraction)
- MULTADDSUBSUM (Multiply, Addition/Subtraction, Summation)

Table 2.7 shows the capabilities of each of the ECP5/ECP5-5G slices versus the above functions.

Table 2.7. Maximum Number of Elements in a Slice

Width of Multiply	x9	x18	x36
MULT	4	2	1/2
MAC	1	1	—
MULTADDSUB	2	1	—
MULTADDSUBSUM	1*	1/2	—

***Note**: One slice can implement 1/2 9x9 m9x9addsubsum and two m9x9addsubsum with two slices.

Some options are available in the four elements. The input register in all the elements can be directly loaded or can be loaded as a shift register from previous operand registers. By selecting “dynamic operation” the following operations are possible:

- In the Add/Sub option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

For further information, refer to ECP5 and ECP5-5G sysDSP Usage Guide (TN1267).

2.10. Programmable I/O Cells

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the ECP5/ECP5-5G devices, the Programmable I/O cells (PIC) are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the ECP5/ECP5-5G devices, two adjacent PIOs can be combined to provide a complementary output driver pair. All PIO pairs can implement differential receivers. Half of the PIO pairs on the left and right edges of these devices can be configured as true LVDS transmit pairs.

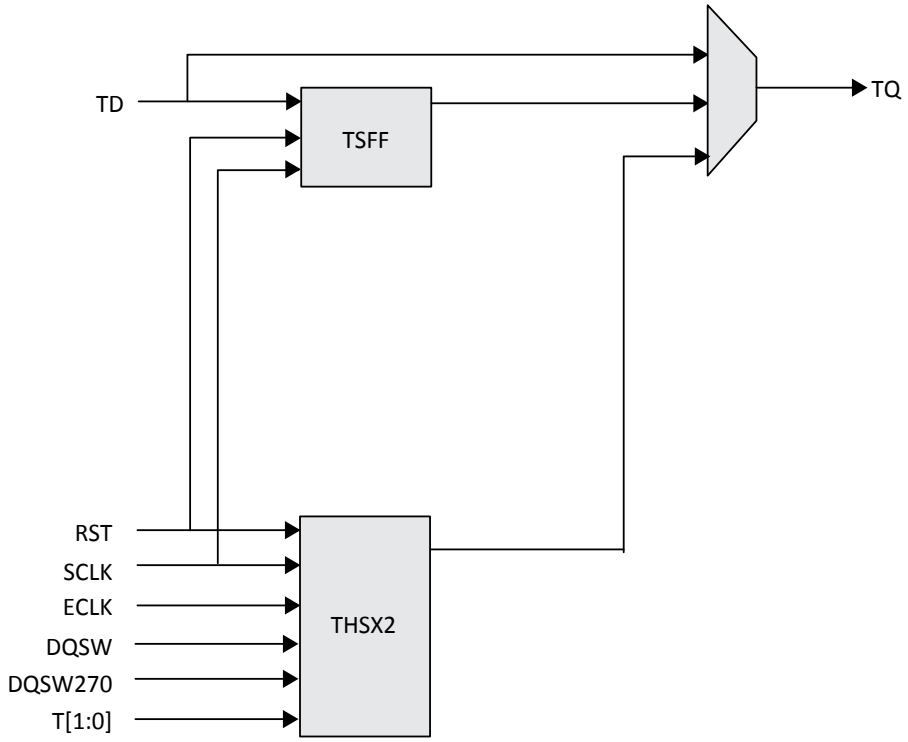

Figure 2.22. Tristate Register Block on Left and Right Sides

Table 2.10. Tristate Block Port Description

Name	Type	Description
TD	Input	Tristate Input to Tristate SDR Register
RST	Input	Reset to the Tristate Block
TD[1:0]	Input	Tristate input to TSHX2 function
SCLK	Input	Slow Speed System Clock
ECLK	Input	High Speed Edge Clock
DQSW	Input	Clock from DQS control Block used to generate DDR memory DQS output
DQSW270	Input	Clock from DQS control Block used to generate DDR memory DQ output
TQ	Output	Output of the Tristate block

2.13. DDR Memory Support

2.13.1. DQS Grouping for DDR Memory

Certain PICs have additional circuitry to allow the implementation of high-speed source synchronous and DDR2, DDR3, LPDDR2 or LPDDR3 memory interfaces. The support varies by the edge of the device as detailed below.

The left and right sides of the PIC have fully functional elements supporting DDR2, DDR3, LPDDR2 or LPDDR3 memory interfaces. Every 16 PIOs on the left and right sides are grouped into one DQS group, as shown in Figure 2.23 on page 36. Within each DQS group, there are two pre-placed pins for DQS and DQS# signals. The rest of the pins in the DQS group can be used as DQ signals and DM signal. The number of pins in each DQS group bonded out is package dependent. DQS groups with less than 11 pins bonded out can only be used for LPDDR2/3 Command/ Address busses. In DQS groups with more than 11 pins bonded out, up to two pre-defined pins are assigned to be used as "virtual" VCCIO, by driving these pins to HIGH, with the user connecting these pins to VCCIO power supply. These connections create "soft" connections to V_{CCIO} thru these output pins, and make better connections on VCCIO to help to reduce SSO noise. For details, refer to ECP5 and ECP5-5G High-Speed I/O Interface (TN1265).

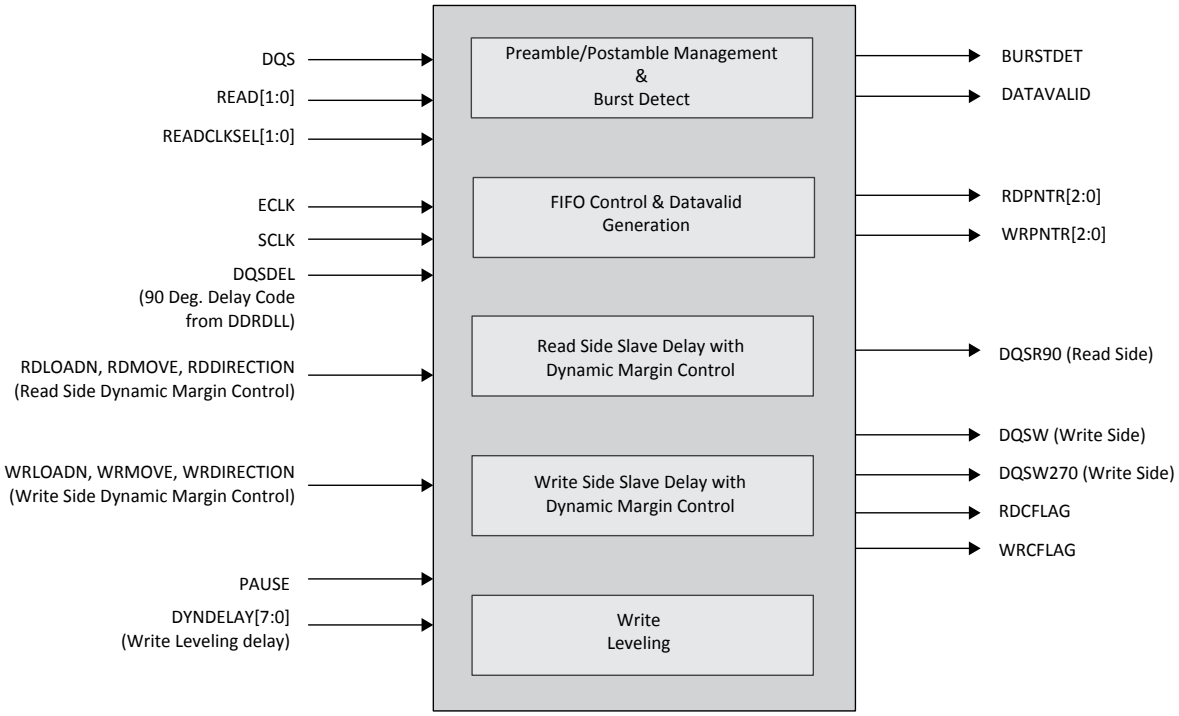

Figure 2.24. DQS Control and Delay Block (DQSBUF)

Table 2.11. DQSBUF Port List Description

Name	Type	Description
DQS	Input	DDR memory DQS strobe
READ[1:0]	Input	Read Input from DDR Controller
READCLKSEL[1:0]	Input	Read pulse selection
SCLK	Input	Slow System Clock
ECLK	Input	High Speed Edge Clock (same frequency as DDR memory)
DQSDEL	Input	90° Delay Code from DDRDLL
RDLOADN, RDMOVE, RDDIRECTION	Input	Dynamic Margin Control ports for Read delay
WRLOADN, WRMOVE, WRDIRECTION	Input	Dynamic Margin Control ports for Write delay
PAUSE	Input	Used by DDR Controller to Pause write side signals during DDRDLL Code update or Write Leveling
DYNDELAY[7:0]	Input	Dynamic Write Leveling Delay Control
DQSR90	Output	90° delay DQS used for Read
DQSW270	Output	90° delay clock used for DQ Write
DQSW	Output	Clock used for DQS Write
RDPNTR[2:0]	Output	Read Pointer for IFIFO module
WRPNTR[2:0]	Output	Write Pointer for IFIFO module
DATAVALID	Output	Signal indicating start of valid data
BURSTDET	Output	Burst Detect indicator
RDFLAG	Output	Read Dynamic Margin Control output to indicate max value
WRFLAG	Output	Write Dynamic Margin Control output to indicate max value

2.14. sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, HSUL, BLVDS, SSTL Class I and II, LVCMOS, LVTTL, LVPECL, and MIPI.

2.14.1. sysI/O Buffer Banks

ECP5/ECP5-5G devices have seven sysI/O buffer banks, two banks per side at Top, Left and Right, plus one at the bottom left side. The bottom left side bank (Bank 8) is a shared I/O bank. The I/Os in that bank contains both dedicated and shared I/O for sysConfig function. When a shared pin is not used for configuration, it is available as a user I/O. For LFE5-85 devices, there is an additional I/O bank (Bank 4) that is not available in other device in the family.

In ECP5/ECP5-5G devices, the Left and Right sides are tailored to support high performance interfaces, such as DDR2, DDR3, LPDDR2, LPDDR3 and other high speed source synchronous standards. The banks on the Left and Right sides of the devices feature LVDS input and output buffers, data-width gearing, and DQSBUF block to support DDR2/3 and LPDDR2/3 interfaces. The I/Os on the top and bottom banks do not have LVDS input and output buffer, and gearing logic, but can use LVCMOS to emulate most of differential output signaling.

Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, the banks on the Left and Right sides of the device, have voltage reference input (shared I/O pin), VREF1 per bank, which allow it to be completely independent of each other. The V_{REF} voltage is used to set the threshold for the referenced input buffers, such as SSTL. Figure 2.25 shows the seven banks and their associated supplies.

In ECP5/ECP5-5G devices, single-ended output buffers and ratioed input buffers (LVTTL, and LVCMOS) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

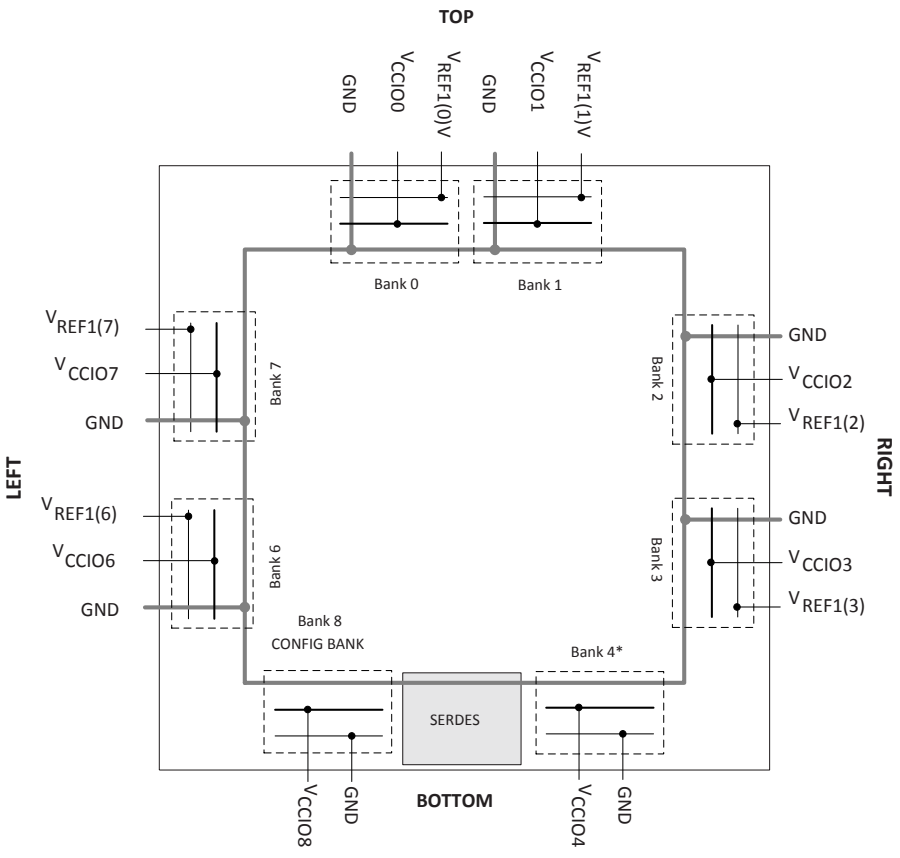

Figure 2.25. ECP5/ECP5-5G Device Family Banks

ECP5/ECP5-5G devices contain two types of sysI/O buffer pairs:

- Top (Bank 0 and Bank 1) and Bottom (Bank 8 and Bank 4) sysIO Buffer Pairs (Single-Ended Only)

  The sysI/O buffers in the Banks at top and bottom of the device consist of ratioed single-ended output drivers and single-ended input buffers. The I/Os in these banks are not usually used as a pair, except when used as emulated differential output pair. They are used as individual I/Os and be configured as different I/O modes, as long as they are compatible with the V_{CCIO} voltage in the bank. When used as emulated differential outputs, the pair can be used together.

  The top and bottom side IOs also support hot socketing. They support IO standards from 3.3 V to 1.2 V. They are ideal for general purpose I/Os, or as ADDR/CMD bus for DDR2/DDR3 applications, or for used as emulated differential signaling.

  Bank 4 I/O only exists in the LFE5-85 device.

  Bank 8 is a bottom bank that shares with sysConfig I/Os. During configuration, these I/Os are used for programming the device. Once the configuration is completed, these I/Os can be released and user can use these I/Os for functional signals in his design.

  The top and bottom side pads can be identified by the Lattice Diamond tool.

- Left and Right (Banks 2, 3, 6 and 7) sysI/O Buffer Pairs (50% Differential and 100% Single-Ended Outputs)

  The sysI/O buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two single-ended input buffers (both ratioed and referenced) and half of the sysI/O buffer pairs (PIOA/B pairs) also has a high-speed differential output driver. One of the referenced input buffers can also be configured as a differential input. In these banks the two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

  In addition, programmable on-chip input termination (parallel or differential, static or dynamic) is supported on these sides, which is required for DDR3 interface. However, there is no support for hot-socketing for the I/O pins located on the left and right side of the device as the PCI clamp is always enabled on these pins.

  LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

2.14.2. Typical sysI/O I/O Behavior during Power-up

The internal Power-On-Reset (POR) signal is deactivated when V_{CC}, V_{CCIO8} and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user’s responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. For more information about controlling the output logic state with valid input logic levels during power-up in ECP5/ECP5-5G devices, see the list of technical documentation in Supplemental Information section on page 102.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

2.14.3. Supported sysI/O Standards

The ECP5/ECP5-5G sysI/O buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, slew rates, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSUL. Differential standards supported include LVDS, differential SSTL and differential HSUL. For further information on utilizing the sysI/O buffer to support a variety of standards, refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262).

3.11. SERDES Power Supply Requirements[1,2,3]

Over recommended operating conditions.

Table 3.9. ECP5UM

Symbol	Description	Typ	Max	Unit
Standby (Power Down)				
I_{CCA-SB}	V_{CCA} Power Supply Current (Per Channel)	4	9.5	mA
$I_{CCHRX-SB}$[4]	V_{CCHRX}, Input Buffer Current (Per Channel)	—	0.1	mA
$I_{CCHTX-SB}$	V_{CCHTX}, Output Buffer Current (Per Channel)	—	0.9	mA
Operating (Data Rate = 3.125 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	43	54	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 2.5 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	40	50	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 1.25 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	34	43	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 270 Mb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	28	38	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	8	10	mA

Notes:

1. Rx Equalization enabled, Tx De-emphasis (pre-cursor and post-cursor) disabled
2. Per Channel current is calculated with both channels on in a Dual, and divide current by two. If only one channel is on, current will be higher.
3. To calculate with Tx De-emphasis enabled, use the Diamond Power Calculator tool.
4. For $I_{CCHRX-SB}$, during Standby, input termination on Rx are disabled.
5. For $I_{CCHRX-OP}$, during operational, the max specified when external AC coupling is used. If externally DC coupled, the power is based on current pulled down by external driver when the input is driven to LOW.

3.14.5. **BLVDS25**

The ECP5/ECP5-5G devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3.2 is one possible solution for bi-directional multi-point differential signals.

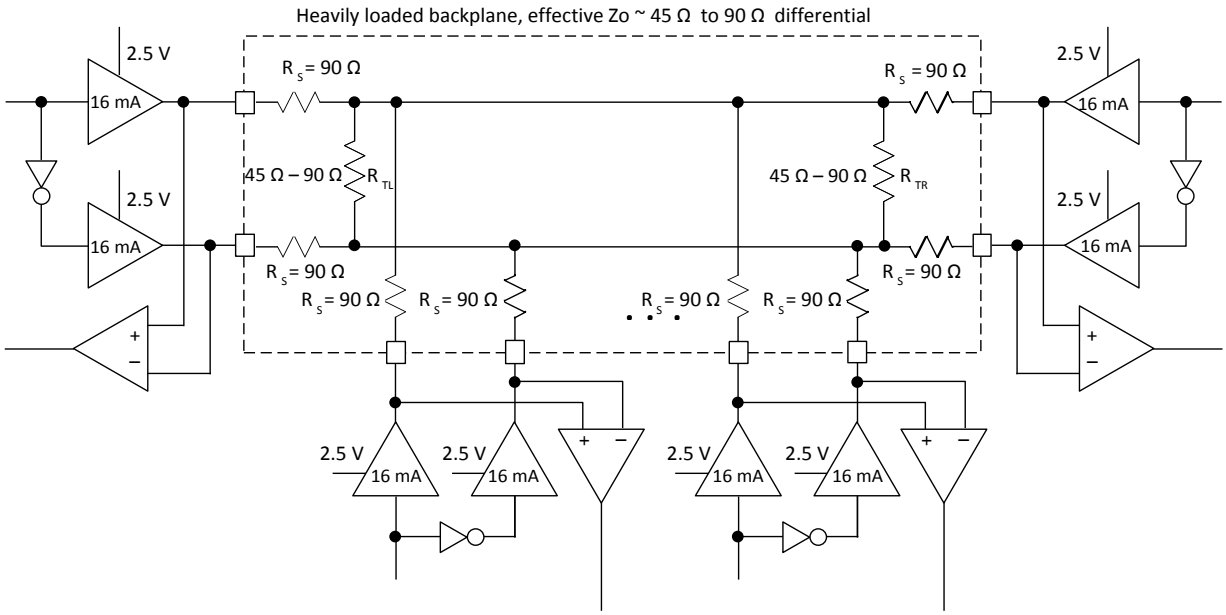

Figure 3.2. BLVDS25 Multi-point Output Example

Over recommended operating conditions.

Table 3.15. BLVDS25 DC Conditions

Parameter	Description	Typical		Unit
		Zo = 45 Ω	Zo = 90 Ω	
V_{CCIO}	Output Driver Supply (±5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (±1%)	90.00	90.00	Ω
R_{TL}	Driver Parallel Resistor (±1%)	45.00	90.00	Ω
R_{TR}	Receiver Termination (±1%)	45.00	90.00	Ω
V_{OH}	Output High Voltage	1.38	1.48	V
V_{OL}	Output Low Voltage	1.12	1.02	V
V_{OD}	Output Differential Voltage	0.25	0.46	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	11.24	10.20	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

3.15. Typical Building Block Function Performance

Table 3.19. Pin-to-Pin Performance

Function	–8 Timing	Unit
Basic Functions		
16-Bit Decoder	5.06	ns
32-Bit Decoder	6.08	ns
64-Bit Decoder	5.06	ns
4:1 Mux	4.45	ns
8:1 Mux	4.63	ns
16:1 Mux	4.81	ns
32:1 Mux	4.85	ns

Notes:

1. I/Os are configured with LVCMOS25 with V_{CCIO}=2.5, 12 mA drive.
2. These functions were generated using Lattice Diamond design software tool. Exact performance may vary with the device and the design software tool version. The design software tool uses internal parameters that have been characterized but are not tested on every device.
3. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from Lattice Diamond design software tool.

3.17. Maximum I/O Buffer Speed

Over recommended operating conditions.

Table 3.21. ECP5/ECP5-5G Maximum I/O Buffer Speed

Buffer	Description	Max	Unit
Maximum Input Frequency			
LVDS25	LVDS, V_{CCIO} = 2.5 V	400	MHz
MLVDS25	MLVDS, Emulated, V_{CCIO} = 2.5 V	400	MHz
BLVDS25	BLVDS, Emulated, V_{CCIO} = 2.5 V	400	MHz
MIPI D-PHY (HS Mode)	MIPI Video	400	MHz
SLVS	SLVS similar to MIPI	400	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, V_{CCIO} = 3.3 V	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, V_{CCIO} = 1.8 V	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, V_{CCIO} = 1.5 V	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, V_{CCIO} = 1.35 V	400	MHz
HSUL12 (all supported classes)	HSUL_12 class I, II, V_{CCIO} = 1.2 V	400	MHz
LVTTL33	LVTTL, V_{CCIO} = 3.3 V	200	MHz
LVCMOS33	LVCMOS, V_{CCIO} = 3.3 V	200	MHz
LVCMOS25	LVCMOS, V_{CCIO} = 2.5 V	200	MHz
LVCMOS18	LVCMOS, V_{CCIO} = 1.8 V	200	MHz
LVCMOS15	LVCMOS 1.5, V_{CCIO} = 1.5 V	200	MHz
LVCMOS12	LVCMOS 1.2, V_{CCIO} = 1.2 V	200	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, V_{CCIO} = 2.5 V	150	MHz
LVDS25	LVDS, V_{CCIO} = 2.5 V	400	MHz
MLVDS25	MLVDS, Emulated, V_{CCIO} = 2.5 V	150	MHz
BLVDS25	BLVDS, Emulated, V_{CCIO} = 2.5 V	150	MHz
LVPECL33	LVPECL, Emulated, V_{CCIO} = 3.3 V	150	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, V_{CCIO} = 1.8 V	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, V_{CCIO} = 1.5 V	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, V_{CCIO} = 1.35 V	400	MHz
HSUL12 (all supported classes)	HSUL12 class I, II, V_{CCIO} = 1.2 V	400	MHz
LVTTL33	LVTTL, VCCIO = 3.3 V	150	MHz
LVCMOS33 (For all drives)	LVCMOS, 3.3 V	150	MHz
LVCMOS25 (For all drives)	LVCMOS, 2.5 V	150	MHz
LVCMOS18 (For all drives)	LVCMOS, 1.8 V	150	MHz
LVCMOS15 (For all drives)	LVCMOS, 1.5 V	150	MHz
LVCMOS12 (For all drives)	LVCMOS, 1.2 V	150	MHz

Notes:

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in Switching Test Conditions, Table 3.44 on page 90.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

3.24. SERDES External Reference Clock

The external reference clock selection and its interface are a critical part of system applications for this product. Table 3.29 specifies reference clock requirements, over the full range of operating conditions.

Table 3.29. External Reference Clock Specification (refclkp/refclkn)

Symbol	Description	Min	Typ	Max	Unit
F_{REF}	Frequency range	50	—	320	MHz
$F_{REF-PPM}$	Frequency tolerance[1]	–1000	—	1000	ppm
$V_{REF-IN-SE}$	Input swing, single-ended clock[2, 4]	200	—	V_{CCAUXA}	mV, p-p
$V_{REF-IN-DIFF}$	Input swing, differential clock	200	—	$2*V_{CCAUXA}$	mV, p-p differential
V_{REF-IN}	Input levels	0	—	V_{CCAUXA} + 0.4	V
D_{REF}	Duty cycle[3]	40	—	60	%
T_{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T_{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
$Z_{REF-IN-TERM-DIFF}$	Differential input termination	–30%	100/HiZ	+30%	Ω
$C_{REF-IN-CAP}$	Input capacitance	—	—	7	pF

Notes:

1. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261).
2. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. With single-ended clock, a reference voltage needs to be externally connected to CLKREFN pin, and the input voltage needs to be swung around this reference voltage.
3. Measured at 50% amplitude.
4. Single-ended clocking is achieved by applying a reference voltage V_{REF} on REFCLKN input, with the clock applied to REFCLKP input pin. V_{REF} should be set to mid-point of the REFCLKP voltage swing.

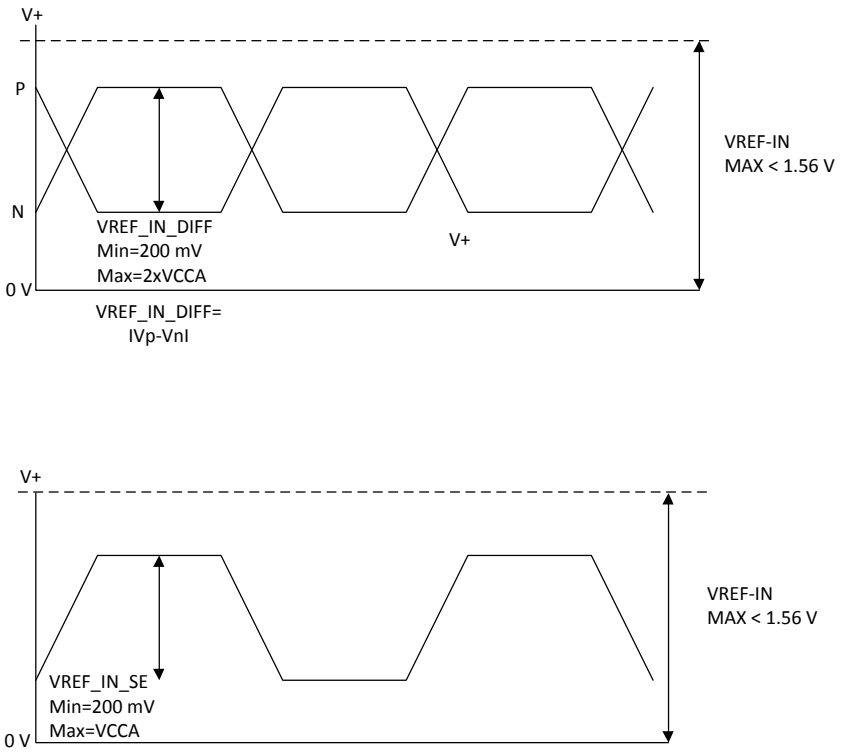

Figure 3.14. SERDES External Reference Clock Waveforms

3.25.2. PCIe (5 Gb/s) – Preliminary AC and DC Characteristics

Over recommended operating conditions.

Table 3.31. PCIe (5 Gb/s)

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit[1]						
UI	Unit Interval	—	199.94	200	200.06	ps
$B_{WTX-PKG-PLL2}$	Tx PLL bandwidth corresponding to PKGTX-PLL2	—	5	—	16	MHz
$P_{KGTX-PLL2}$	Tx PLL Peaking	—	—	—	1	dB
$V_{TX-DIFF-PP}$	Differential p-p Tx voltage swing	—	0.8	—	1.2	V, p-p
$V_{TX-DIFF-PP-LOW}$	Low power differential p-p Tx voltage swing	—	0.4	—	1.2	V, p-p
$V_{TX-DE-RATIO-3.5dB}$	Tx de-emphasis level ratio at 3.5dB	—	3	—	4	dB
$V_{TX-DE-RATIO-6dB}$	Tx de-emphasis level ratio at 6dB	—	5.5	—	6.5	dB
$T_{MIN-PULSE}$	Instantaneous lone pulse width	—		—	—	UI
$T_{TX-RISE-FALL}$	Transmitter rise and fall time	—		—	—	UI
T_{TX-EYE}	Transmitter Eye, including all jitter sources	—	0.75	—	—	UI
T_{TX-DJ}	Tx deterministic jitter > 1.5 MHz	—	—	—	0.15	UI
T_{TX-RJ}	Tx RMS jitter < 1.5 MHz	—	—	—	3	ps, RMS
$T_{RF-MISMATCH}$	Tx rise/fall time mismatch	—	—	—		UI
$R_{LTX-DIFF}$	Tx Differential Return Loss, including package and silicon	50 MHz < freq < 1.25 GHz	10	—	—	dB
		1.25 GHz < freq < 2.5 GHz	8	—	—	dB
R_{LTX-CM}	Tx Common Mode Return Loss, including package and silicon	50 MHz < freq < 2.5 GHz	6	—	—	dB
$Z_{TX-DIFF-DC}$	DC differential Impedance	—	—	—	120	Ω
$V_{TX-CM-AC-PP}$	Tx AC peak common mode voltage, peak-peak	—	—	—		mV, p-p
$I_{TX-SHORT}$	Transmitter short-circuit current	—	—	—	90	mA
$V_{TX-DC-CM}$	Transmitter DC common-mode voltage	—	0	—	1.2	V
$V_{TX-IDLE-DIFF-DC}$	Electrical Idle Output DC voltage	—	0	—	5	mV
$V_{TX-IDLE-DIFF-AC-p}$	Electrical Idle Differential Output peak voltage	—	—	—		mV
$V_{TX-RCV-DETECT}$	Voltage change allowed during Receiver Detect	—	—	—	600	mV
$T_{TX-IDLE-MIN}$	Min. time in Electrical Idle	—	20	—	—	ns
$T_{TX-IDLE-SET-TO-IDLE}$	Max. time from EI Order Set to valid Electrical Idle	—	—	—	8	ns
$T_{TX-IDLE-TO-DIFF-DATA}$	Max. time from Electrical Idle to valid differential output	—	—	—	8	ns
$L_{TX-SKEW}$	Lane-to-lane output skew	—	—	—		ps

3.31. sysCONFIG Port Timing Specifications

Over recommended operating conditions.

Table 3.42. ECP5/ECP5-5G sysCONFIG Port Timing Specifications

Symbol	Parameter		Min	Max	Unit
POR, Configuration Initialization, and Wakeup					
t_{ICFG}	Time from the Application of V_{CC}, V_{CCAUX} or V_{CCIO8} (whichever is the last) to the rising edge of INITN	—	—	33	ms
t_{VMC}	Time from t_{ICFG} to the valid Master CCLK	—	—	5	us
t_{CZ}	CCLK from Active to High-Z	—	—	300	ns
Master CCLK					
f_{MCLK}	Frequency	All selected frequencies	–20	20	%
$t_{MCLK-DC}$	Duty Cycle	All selected frequencies	40	60	%
All Configuration Modes					
t_{PRGM}	PROGRAMN LOW pulse accepted	—	110	—	ns
t_{PRGMRJ}	PROGRAMN LOW pulse rejected	—	—	50	ns
t_{INITL}	INITN LOW time	—	—	55	ns
t_{DPPINT}	PROGRAMN LOW to INITN LOW	—	—	70	ns
$t_{DPPDONE}$	PROGRAMN LOW to DONE LOW	—	—	80	ns
t_{IODISS}	PROGRAMN LOW to I/O Disabled	—	—	150	ns
Slave SPI					
f_{CCLK}	CCLK input clock frequency	—	—	60	MHz
t_{CCLKH}	CCLK input clock pulsewidth HIGH	—	6	—	ns
t_{CCLKL}	CCLK input clock pulsewidth LOW	—	6	—	ns
t_{STSU}	CCLK setup time	—	1	—	ns
t_{STH}	CCLK hold time	—	1	—	ns
t_{STCO}	CCLK falling edge to valid output	—	—	10	ns
t_{STOZ}	CCLK falling edge to valid disable	—	—	10	ns
t_{STOV}	CCLK falling edge to valid enable	—	—	10	ns
t_{SCS}	Chip Select HIGH time	—	25	—	ns
t_{SCSS}	Chip Select setup time	—	3	—	ns
t_{SCSH}	Chip Select hold time	—	3	—	ns
Master SPI					
f_{CCLK}	Max selected CCLK output frequency	—	—	62	MHz
t_{CCLKH}	CCLK output clock pulse width HIGH	—	3.5	—	ns
t_{CCLKL}	CCLK output clock pulse width LOW	—	3.5	—	ns
t_{STSU}	CCLK setup time	—	5	—	ns
t_{STH}	CCLK hold time	—	1	—	ns
t_{CSSPI}	INITN HIGH to Chip Select LOW	—	100	200	ns
t_{CFGX}	INITN HIGH to first CCLK edge	—	—	150	ns
Slave Serial					
f_{CCLK}	CCLK input clock frequency	—	—	66	MHz
t_{SSCH}	CCLK input clock pulse width HIGH	—	5	—	ns
t_{SSCL}	CCLK input clock pulse width LOW	—	5	—	ns
t_{SUSCDI}	CCLK setup time	—	0.5	—	ns
t_{HSCDI}	CCLK hold time	—	1.5	—	ns

Table 3.44. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L ≥ H, H ≥ L)	∞	∞	0 pF	LVCMOS 3.3 = 1.5 V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z ≥ H)	∞	1 MΩ	0 pF	$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z ≥ L)	1 MΩ	∞	0 pF	$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H ≥ Z)	∞	100	0 pF	V_{OH} – 0.10	—
LVCMOS 2.5 I/O (L ≥ Z)	100	∞	0 pF	V_{OL} + 0.10	V_{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

4.3.2. LFE5U

Pin Information Summary		LFE5U-12			LFE5U-25			LFE5U-45				LFE5U-85			
Pin Type		256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	554 caBGA	285 csfBG	381 caBGA	554 caBGA	756 caBG
General Purpose Inputs/Outputs per Bank	Bank 0	24	6	24	24	6	24	24	6	27	32	6	27	32	56
	Bank 1	32	6	32	32	6	32	32	6	33	40	6	33	40	48
	Bank 2	32	21	32	32	21	32	32	21	32	32	21	34	32	48
	Bank 3	32	28	32	32	28	32	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	14	24
	Bank 6	32	26	32	32	26	32	32	26	33	48	26	33	48	64
	Bank 7	32	18	32	32	18	32	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13	13	13	13	13	13
Total Single-Ended User		197	118	197	197	118	197	197	118	203	245	118	205	259	365
VCC		6	13	20	6	13	20	6	13	20	24	13	20	24	36
VCCAUX (Core)		2	3	4	2	3	4	2	3	4	9	3	4	9	8
VCCIO	Bank 0	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 1	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 2	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 3	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	2	2
	Bank 6	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 7	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 8	1	2	2	1	2	2	1	2	2	2	2	2	2	2
TAP		4	4	4	4	4	4	4	4	4	4	4	4	4	4
Miscellaneous Dedicated		7	7	7	7	7	7	7	7	7	7	7	7	7	7
GND		27	123	99	27	123	99	27	123	99	198	123	99	198	267
NC		0	1	26	0	1	26	0	1	26	33	1	26	33	29
Reserved		0	4	6	0	4	6	0	4	6	12	4	6	12	12
Total Balls		256	285	381	256	285	381	256	285	381	554	285	381	554	756
High Speed Differential Input / Output Pairs	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	17/9	16/8	
	Bank	16/8	14/7	16/8	16/8	14/7	16/8	16/8	14/7	16/8	24/12	14/7	16/8	24/1	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	13/6	16/8	16/8	13/6	16/8	16/8	13/6	16/8	24/12	13/6	16/8	24/1	
	Bank	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total High Speed		64/32	45/27	64/32	64/32	45/27	64/32	64/32	45/27	64/32	80/40	45/27	65/33	80/40	112/
DQS Groups (> 11 pins in group)	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total DQS Groups		8	6	8	8	6	8	8	6	8	10	6	8	10	14

Supplemental Information

For Further Information

A variety of technical notes for the ECP5/ECP5-5G family are available.

- High-Speed PCB Design Considerations (TN1033)
- Transmission of High-Speed Serial Signals Over Common Cable Media (TN1066)
- PCB Layout Recommendations for BGA Packages (TN1074)
- Minimizing System Interruption During Configuration Using TransFR Technology (TN1087)
- Electrical Recommendations for Lattice SERDES (FPGA-TN-02077)
- LatticeECP3, ECP-5 and ECP5-5G Soft Error Detection (SED)/Correction (SEC) Usage Guide (TN1184)
- Using TraceID (TN1207)
- Sub-LVDS Signaling Using Lattice Devices (TN1210)
- Advanced Security Encryption Key Programming Guide for ECP5, ECP5-5G, LatticeECP3, and LatticeECP2/MS Devices (TN1215)
- LatticeECP3, LatticeECP2/M, ECP5 and ECP5-5G Dual Boot and Multiple Boot Feature (TN1216)
- ECP5 and ECP5-5G sysCONFIG Usage Guide (TN1260)
- ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261)
- ECP5 and ECP5-5G sysIO Usage Guide (TN1262)
- ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide (TN1263)
- ECP5 and ECP5-5G Memory Usage Guide (TN1264)
- ECP5 and ECP5-5G High-Speed I/O Interface (TN1265)
- Power Consumption and Management for ECP5 and ECP5-5G Devices (TN1266)
- ECP5 and ECP5-5G sysDSP Usage Guide (TN1267)
- ECP5 and ECP5-5G Hardware Checklist (FPGA-TN-02038)
- Solder Reflow Guide for Surface Mount Devices (FPGA-TN-02041)
- ECP5 and ECP5-5G PCI Express Soft IP Ease of Use Guidelines (FPGA-TN-02045)
- Programming External SPI Flash through JTAG for ECP5/ECP5-5G (FPGA-TN-02050)
- Adding Scalable Power and Thermal Management to ECP5 Using L-ASC10 (AN6095)

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTL, LVCMOS, SSTL): www.jedec.org
- PCI: www.pcisig.com

(Continued)

Date	Version	Section	Change Summary
August 2014	1.2	All	Changed document status from Advance to Preliminary.
		General Description	Updated Features section. • Deleted Serial RapidIO protocol under Embedded SERDES. • Corrected data rate under Pre-Engineered Source Synchronous
			Changed DD3. LPDDR3 to DDR2/3, LPDDR2/3. Mentioned transmit de-emphasis “pre- and post-cursors”.
		Architecture	Updated Overview section. • Revised description of PFU blocks. • Specified SRAM cell settings in describing the control of SERDES/PCS duals.
			Updated SERDES and Physical Coding Sublayer section. • Changed PCI Express 2.0 to PCI Express Gen1 and Gen2. • Deleted Serial RapidIO protocol. • Updated Table 2.13. LFE5UM/LFE5UM5G SERDES Standard Support.
			Updated On-Chip Oscillator section. • Deleted “130 MHz ±15% CMOS” oscillator. • Updated Table 2.16. Selectable Master Clock (MCLK) Frequencies during Configuration (Nominal)
		DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Added supply voltages V_{CCA} and V_{CCAUXA}.
			Updated sysI/O Recommended Operating Conditions section. Revised HSULD12D VCCIO values and removed table note.
			Updated sysI/O Single-Ended DC Electrical Characteristics section. Revised some values for SSTL15 _I, SSTL15 _II, SSTL135_I, SSTL15_II, and HSUL12.
			Updated External Switching Characteristics section. Changed parameters to t_{SKEW_PR} V_{CCA} and t_{SKEW_EDGE} and added LFE5-85 as device.
			Updated ECP5 Family Timing Adders section. Added SSTL135_II buffer type data. Removed LVCMOS33_20mA, LVCMOS25_20mA, LVCMOS25_16mA, LVCMOS25D_16mA, and LVCMOS18_16mA buffer types. Changed buffer type to LVCMOS12_4mA and LVCMOS12_8mA.
			Updated Maximum I/O Buffer Speed section. Revised Max values.
			Updated sysCLOCK PLL Timing section. Revised t_{DT} Min and Max values. Revised t_{OPJIT} Max value. Revised number of samples in table note 1.
			Updated SERDES High-Speed Data Transmitter section. Updated Table 3.24. Serial Output Timing and Levels and Table 3.25. Channel Output Jitter.